

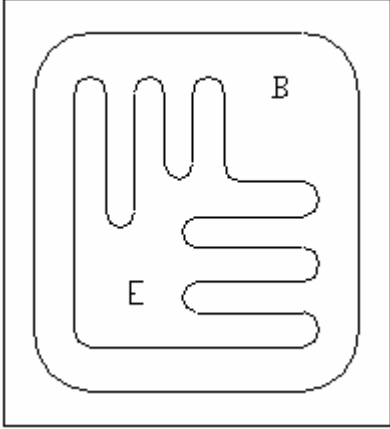
9012B Silicon PNP Epitaxial Transistor

Description :The 9012B is designed for audio frequency general amplifier applications

Features: ●Excellent h_{FE} Linearity

●Complementary to 9013B

Chip Appearance

	Chip Size		490um × 490um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	110um × 110um
	Front Metal		Al
	Backside Metal		Au
	Scribe line width		55um
	Wafer Size		6 inch

Electrical Characteristics($T_a=25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$		-0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-0.1\text{mA}$	-40		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}$	-25		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-0.1\text{mA}$	-5		V
DC Current Gain	h_{FE}	$V_{CE}=-1\text{V}, I_C=-50\text{mA}$	150	400	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$		-0.5	V